



Description

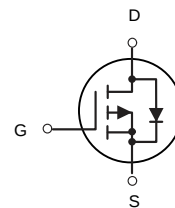
The HXY20P03D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = -30V$ $I_D = -20A$

$R_{DS(ON)} < 42\text{ m}\Omega @ V_{GS}=10V$



P-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HXY20P03D	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	-20	A
$I_D @ T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	-15	A
IDM	Pulsed Drain Current ²	-50	A
$P_D @ T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	29	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	75	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4.32	$^\circ\text{C/W}$



Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	T_p	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-30		---	V
$\Delta BVDSS/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	22	---	$V/^{\circ}\text{C}$
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-15A$	32	38	42	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-10A$	48	60	70	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.0	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	$mV/^{\circ}\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
		$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	-5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 25V$, $V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=-5V$, $I_D=-15A$	---	19	---	S
Rg	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	13	---	
Qg	Total Gate Charge (-4.5V)	$V_{DS}=-15V$, $V_{GS}=-4.5V$, $I_D=-15A$	---	12.5	---	nC
Qgs	Gate-Source Charge		---	5.4	---	
Qgd	Gate-Drain Charge		---	5	---	
Td(on)	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GS}=-10V$, $R_G=3.3\Omega$, $I_D=-15A$	---	4.4	---	ns
Tr	Rise Time		---	11.2	---	
Td(off)	Turn-Off Delay Time		---	34	---	
Tf	Fall Time		---	18	---	
Ciss	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1MHz$	---	1345	---	pF
Coss	Output Capacitance		---	194	---	
Crss	Reverse Transfer Capacitance		---	158	---	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

Figure 5 Output Characteristics

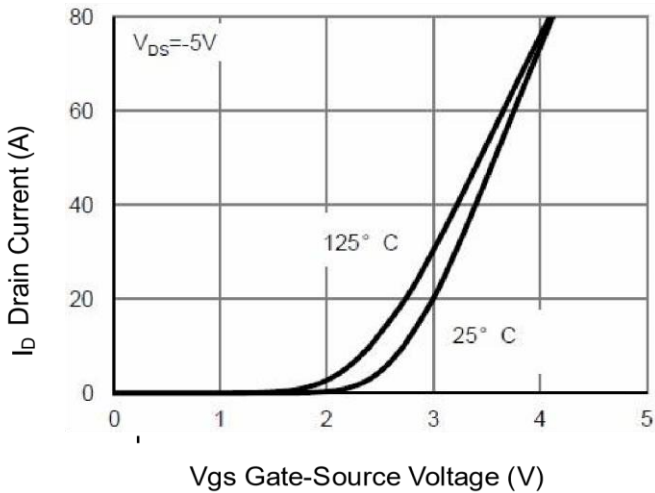


Figure 7 Transfer Characteristics

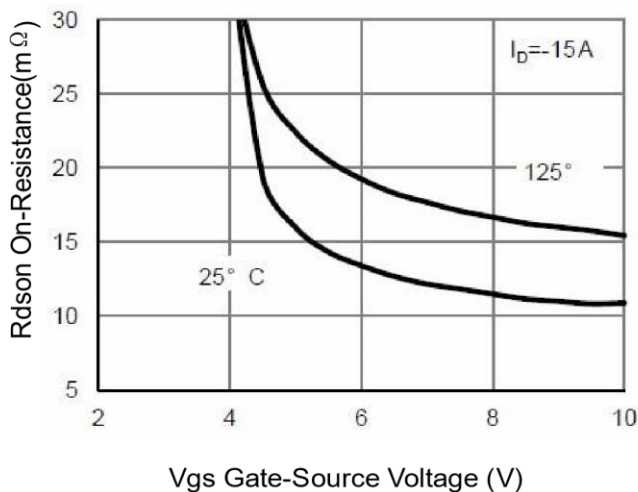


Figure 9 Rdson vs Vgs

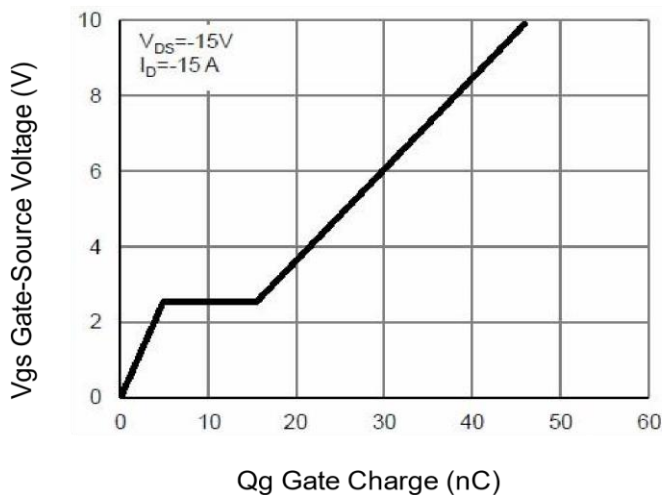


Figure 11 Gate Charge

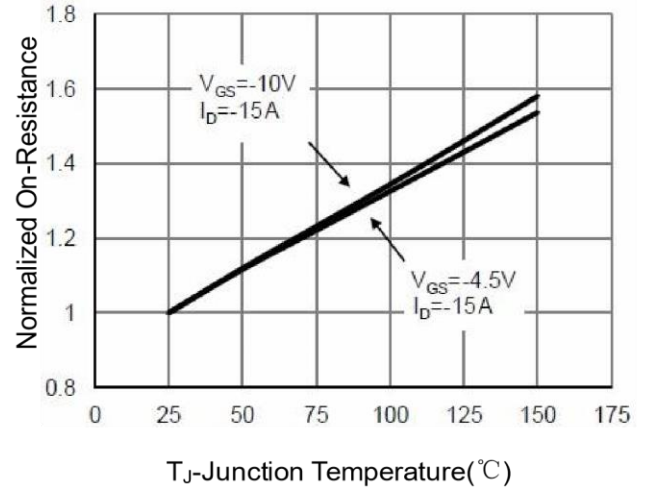


Figure 8 Drain-Source On-Resistance

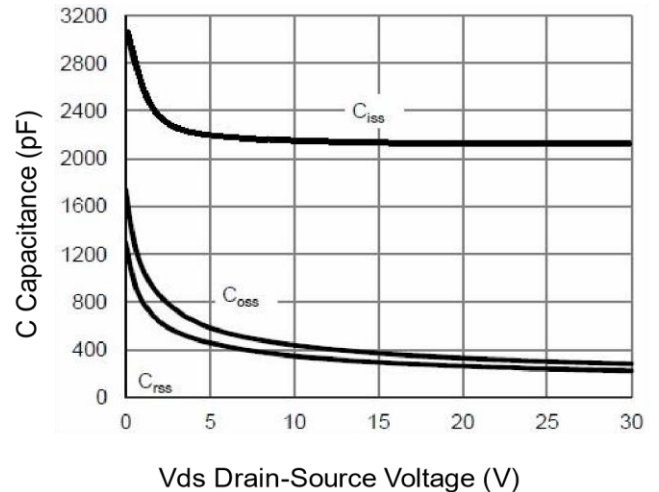


Figure 10 Capacitance vs Vds

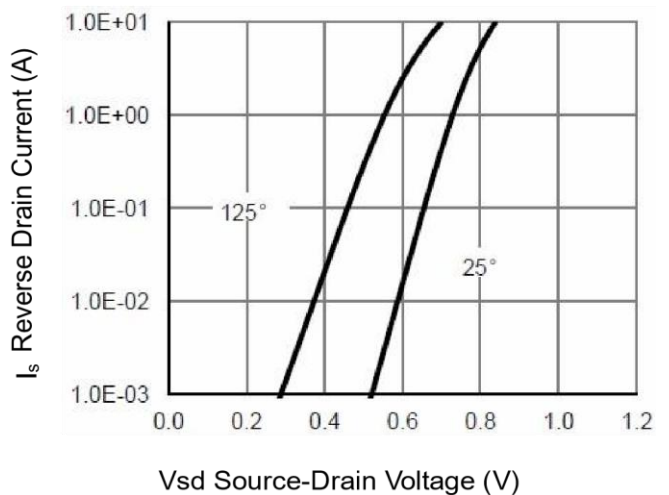


Figure 12 Source- Drain Diode Forward



P-Channel Enhancement Mode MOSFET

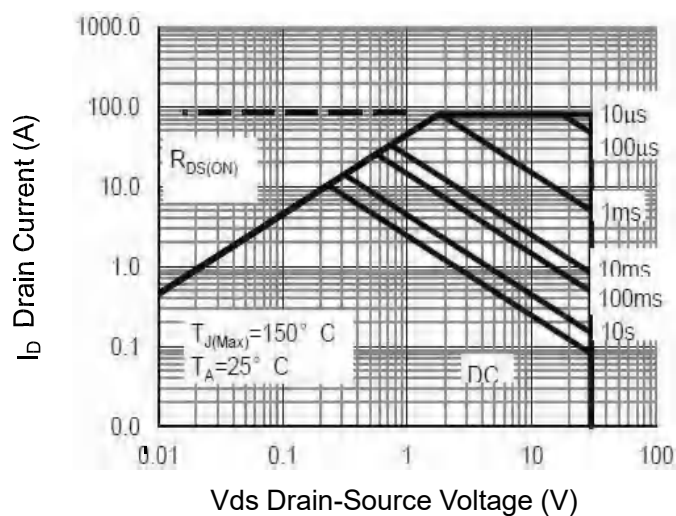


Figure 13 Safe Operation Area

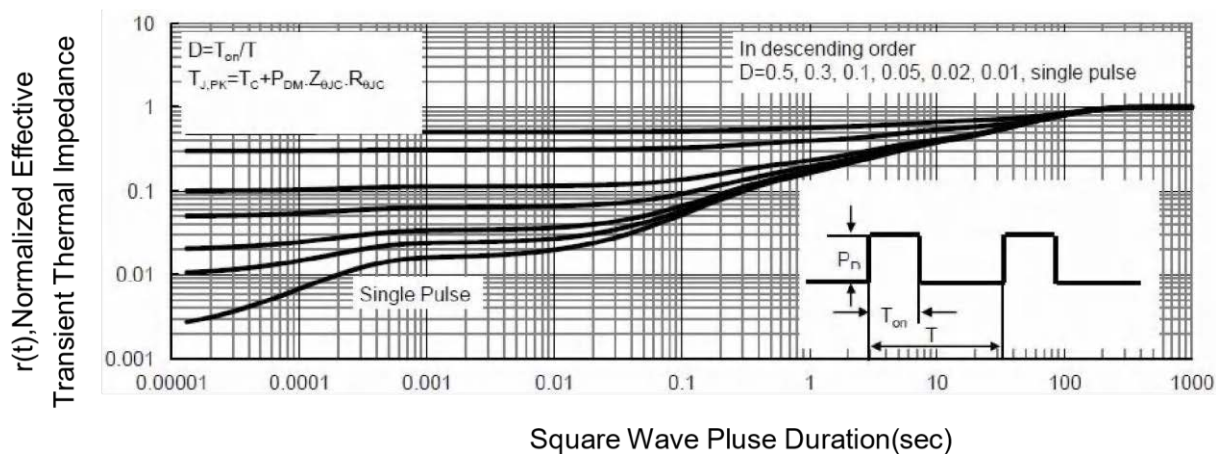
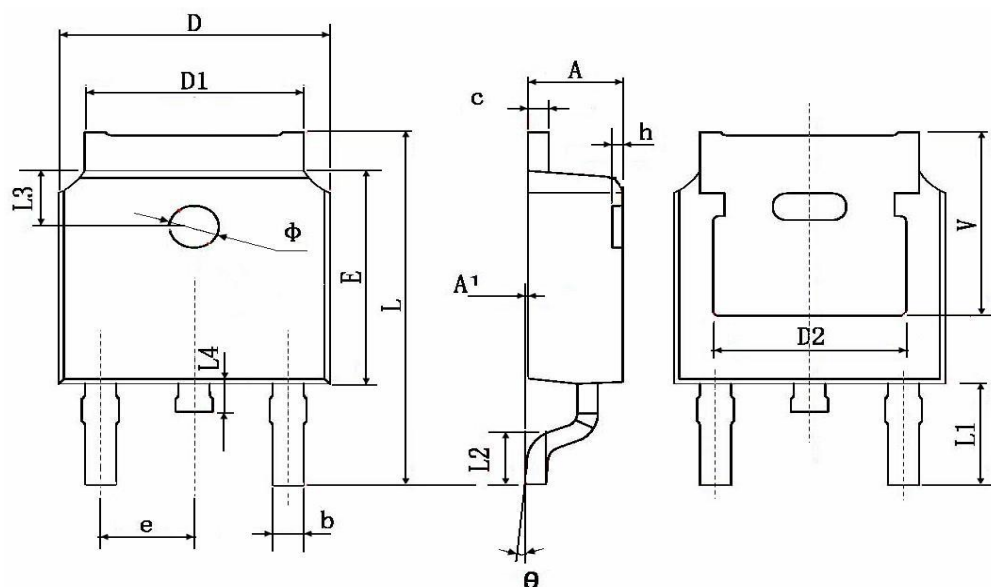


Figure 14 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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